

EAST - (10799380 semi-insul-semi of different crystal orientation.wsp:1)

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Drafts

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Active

- L1: (4) "5384473".pn. "20040018701"
- L2: (103541) n-mos n-mosfet n-fet nmos nmosfet nfet n near2 (transistor t
- L3: (90851) p-mos p-mosfet p-fet pmos pmosfet pfet p near2 (transistor t
- L4: (68791) 2 with 3
- L5: (592441) l (crystal39 surface) near2 (orient38 grow84 face82 facing s
- L6: (3867308) different other
- L7: (18529) 5 near6 6
- L8: (29) 3 same 7
- L9: (622480) nm nanometer nano adj meter angstrom ang ".ang."
- L10: (24) 8 and 9
- L11: (24) 8 and 2 and 3 and 5 and 8

Failed

Saved

- S2: (1) 09/948877
- S3: (1736) "KOHINKLUKE PHILIPS".as.
- S1: (1) 10/750014

6 and 2 and 3 and 5 and 8

May 2005

U	I	Inventor	Document	Issue	P	Title	Current	Current	Retrieval	S	C	P	Image	Doc	P
1		Blum, Kern	US 200500	2005	18	Double silicon-on-insulator (SOI) metal	257/72							US 20050	
2		Goris, Bruce	US 200402	2004	118	High-performance CMOS devices on hy	257/82							US 20040	
3		Yeo, Yee-Ch	US 2004019	2004	118	Silicon-on-insulator chip with multiple	257/52							US 200401	
4		Miyasaka,	US 2004017	2004	9	Complementary thin film transistor cir	257/35							US 200401	
5		Maeda, Shi	US 2004007	2004	2	Semiconductor device and method of	257/34	257/821.41						US 20040	
6		Guarini, Kat	US 683098	2004	112	Self-aligned SOI with different crystal	438/14	438/150;						US 68309	
7		Jeong, Meik	US 200500	2005	27	CMOS on hybrid substrate with differe	257/86							US 20050	
8		Jeong, Meik	US 200500	2005	27	CMOS on hybrid substrate with differe	257/82	257/389;						US 20050	
9		Guarini, Kat	US 200500	2005	12	Self-aligned SOI with different crystal	438/47							US 20050	
10		Chan, Victor	US 200500	2005	8	Three dimensional CMOS integrated ci	257/87	257/74;						US 20050	

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